



JAN and JANTX 1N5614 thru 1N5622

Patented*

Vishay Semiconductors
formerly GENERAL SEMICONDUCTOR®

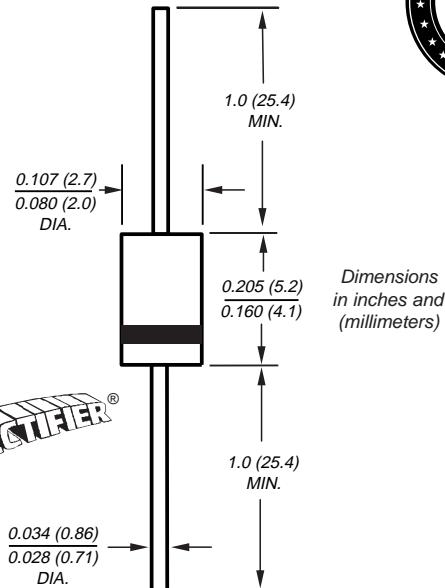
Glass Passivated Rectifiers



DO-204AL (EG1)

Reverse Voltage 200 to 1000V
Forward Current 1.0A

SUPERRECTIFIER®



* Glass-plastic encapsulation technique is covered by Patent No. 3,996,602
and brazed-lead assembly by Patent No. 3,930,306

Features

- Qualified to MIL-PRF-19500/427
- Class 1 high temperature metallurgically bonded construction brazed > 600°C
- 1.0 ampere operation at TA = 55°C with no thermal runaway
- Typical IR less than 0.1µA
- Cavity-free, glass passivated junction. In epoxy over hermetic glass
- High temperature soldering guaranteed: 350°C/10 seconds, 0.375 (9.5mm) lead length, 5 lbs. (2.3kg) tension

Mechanical Data

Case: DO-204AL, molded epoxy over glass body (EG1)

Terminals: Solder plated axial leads, solderable per MIL-STD-750, Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any Weight: 0.015oz., 0.4g

Flammability: Epoxy is rated UL 94V-0.

Maximum Ratings & Thermal Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Prefix J = JAN Quality Level; Prefix JX = JANTX Quality Level					Unit
		J, JX 1N5614	J, JX 1N5616	J, JX 1N5618	J, JX 1N5620	J, JX 1N5622	
Maximum repetitive peak reverse voltage	V _{RRM}	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	140	280	420	560	700	V
Maximum DC blocking voltage	V _{DC}	200	400	600	800	1000	V
Maximum average forward rectified current 0.375" (9.5mm) lead length at TA = 55°C	I _{F(AV)}	1.0					A
Peak forward surge current 10 surges of 8.3ms each at 1 min. intervals super-imposed on I ₀ = 750mA DC; VR = rated V _{RRM} TA = 100°C (per MIL-STD-750 m 4066)	I _{FSM}	25					A
Typical thermal resistance ⁽¹⁾	R _{θJL} R _{θJA}	38 45					°C/W
Operating junction and storage temperature range	T _J , T _{STG}	−65 to +175					°C
Barometric Pressure	Hg	8			33		mm

Electrical Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

Minimum reverse breakdown voltage at 50µA	V _{BR}	220	440	660	880	1100	V
Maximum instantaneous forward voltage T _p = 300µs	at 1.0A at 3.0A	V _F	1.1 1.3				V
Maximum DC reverse current at rated DC blocking voltage	T _A = 25°C T _A = 100°C	I _R	0.5 25				µA
Maximum reverse recovery time at I _F = 0.5A, I _R = 1.0A, I _{rr} = 0.25A	t _{rr}	2.0				µs	
Maximum junction capacitance at 4V, 1MHz	C _J	15				pF	

Notes: (1) Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted

Ratings and Characteristic Curves

($T_A = 25^\circ\text{C}$ unless otherwise noted)

Fig. 1 – Forward Current Derating Curve

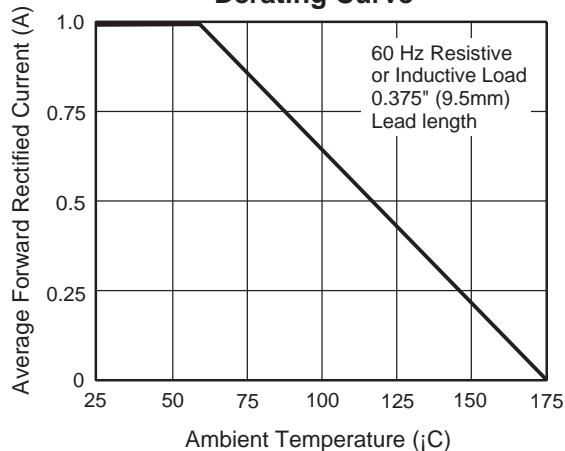


Fig. 2 – Typical Instantaneous Forward Characteristics

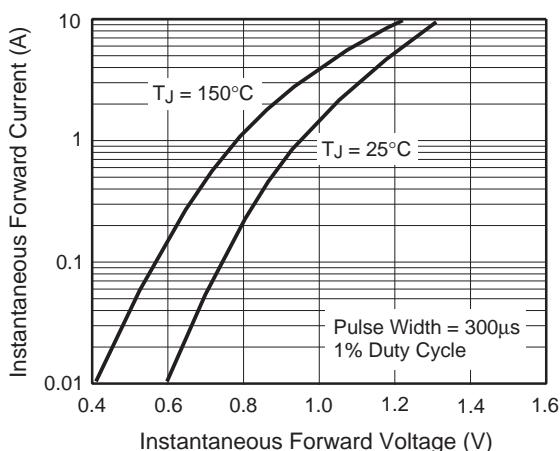


Fig. 3 – Typical Reverse Characteristics

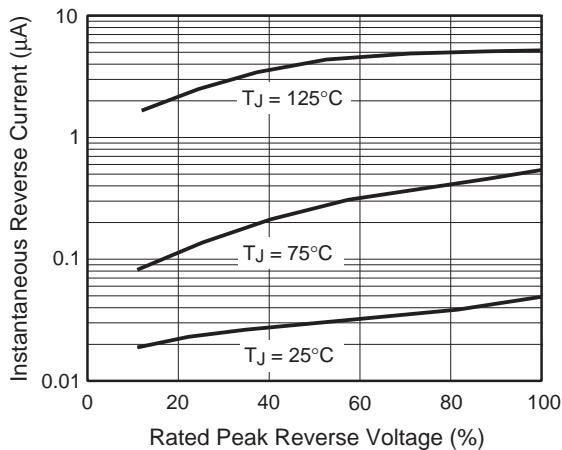


Fig. 4 – Typical Junction Capacitance

